

EAST - [testshu.wsp.1]

File View Edit Tools Window Help

☐ Drafts
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L1: (61319) gate near electrode
 L2: (1828) 1 and (hard adj mask\$1)
 L3: (1562) 2 and (contact or holes1 or opening\$1)
 L4: (1138) 3 and (gate.clm. or electrode.clm.)
 L5: (804) 4 and (mask near10 (gate or electrode))
 L6: (877) 4 and (mask with (gate or electrode))
 L7: (490) 6 and (contact.clm. or opening.clm. or hole.clm.)
 L8: (161) 7 and (LDD or TFT or (thin adj film adj transistor))
 L9: (144) 8 and (mask near10 (gate or electrode))
 L10: (88) 8 and ((hard adj mask) near10 (gate or electrode))
 L11: (3) 10 and (island adj like)
 L12: (87) 10 and LDD
 L13: (32) 10 and (hard adj mask).clm.
 L14: (453) 4 and (contact near6 (opening or hole))
 L15: (427) 14 and ((contact\$3 or connect\$3 or wir\$3) near10 (g
 L16: (295) 15 and (contact.clm.)
 L17: (72) 16 and (hard adj mask).clm.
 L18: (17) 17 and (LDD or TFT)

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Name: []
 Date: []
 Class: [USPAT.US48216]
 Publication: [OR]
 P High/Low/Original/Rev: []

17 and (LDD or TFT)

	U	I	P	T	P	Document ID	Issue Dat	Pages	Title	Current OR	Current OR	Retrieval	Inventor	S	C				
7						US 20030122179	20030703	26	Method of manufacturing a field effect transistor	257/314	257/E21.2;		Matsuki, Takeo et al.						
8						US 20030057455	20030327	21	SOI semiconductor integrated circuit for	257/213	257/E29.28		Kim, Young-Wug et al.						
9						US 20011220	20011220	16	Merged memory and logic semiconductor device of	257/296	257/300;		Kim, Bong-seok						
10						US 20010052611	20011018	33	SOI semiconductor integrated circuit for	438/149	257/E29.28		Kim, Young-Wug et al.						
11						US 6706569	20040316	21	SOI semiconductor integrated circuit for	438/149	257/347;		Kim, Young-Wug et al.						
12						US 6624019	20030923	15	Merged memory and logic semiconductor device of	438/241	257/E21.63		Kim, Bong-seok						
13						US 6541327	20030401	9	Method to form self-aligned source/drain	438/229	257/E21.43		Chan, Lap et al.						
14						US 6316349	20011113	17	Method for forming contacts of semiconductor	438/637	257/401;		Kim, Jeong Ho et al.						
15						US 6214656	20010410	13	Partial silicide gate in gap (self-aligned co	438/199	257/E21.50		Liaw, Jhon-Jhy						
16						US 6080647	20000627	11	Process to form a trench-free buried cont	438/586	257/E21.43		Huang, Kuo-Ching et al.						
17						US 5998269	19991207	13	Technology for high performance buried cont	438/282	257/288;		Huang, Kuo-Ching et al.						

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